



Miniaturized Gate Drive Transformers



- Deliver MOSFET/IGBT gate power and timing signals simultaneously
- Directly drive high-side MOSFETs/IGBTs on busses up to 1200V
- Excellent risetime, overshoot, and peak current characteristics
- >8 mm minimum creepage and clearance from drive to gates
- Low profile planar package
- Available in through-hole and surface mount packages
(contact engineering)

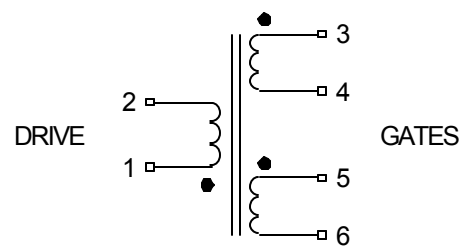
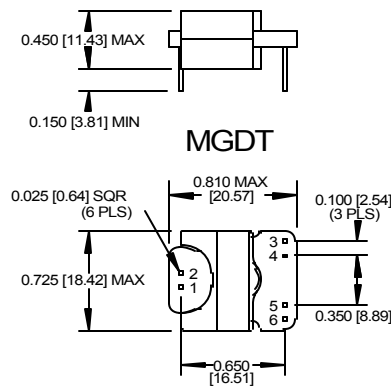
Model Selection Table

HiRel P/N	Package Style	Useful Freq. Range (KHz)	Transfer Ratio ¹ (+/-3%)	Drive Excitation (V•nS MAX)	Magnetizing Inductance ^{2,3} (nH MIN)	Leakage Inductance ⁴ (nH MAX)	DC Resistance ²		Capacitance	
							Drive (W MAX)	Gates (W MAX)	Drive-Gate (pF MAX)	Gate-Gate (pF MAX)
MGDT 100 100	TH	100 ~ 500	1 : 1 : 1	80	240	500	0.50	0.50	15	10

Absolute Maximum Ratings (All Models)

Parameter	Conditions	Limit(s)	Units
Dielectric Withstand Voltage	Drive-gate; 1 min	3750	VAC
	Gate-gate; 1 min	2500	VAC
Total Power Dissipation ⁵	T _A = 25°C	2.0	W
Operating Temperature	Continuous	-40 ~ +85	°C
Storage Temperature	Continuous	-40 ~ +105	°C

1. Drive : Gate : Gate.
2. T_A = 25°C.
3. 100mV @ 100KHz across the Drive winding with all Gates open.
4. 100mA @ 100KHz into the Drive winding with all Gates shorted.
5. Derate at 33.3mW / °C above 25°C.



Units are inches [mm].
Tolerance on all dimensions is +/-0.010 unless otherwise specified.
Specifications are subject to change without notice.

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